

TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC3225

Switching Applications
Solenoid Drive Applications

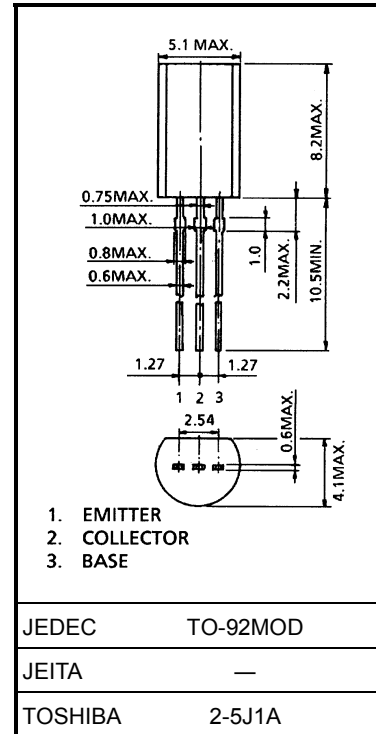
Industrial Applications

Unit: mm

- High DC current gain: $h_{FE} = 500$ (min) ($I_C = 400$ mA)
- Low collector-emitter saturation voltage: $V_{CE(sat)} = 0.5$ V (max) ($I_C = 300$ mA)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	2	A
Base current	I_B	0.5	A
Collector power dissipation	P_C	900	mW
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55 to 150	°C

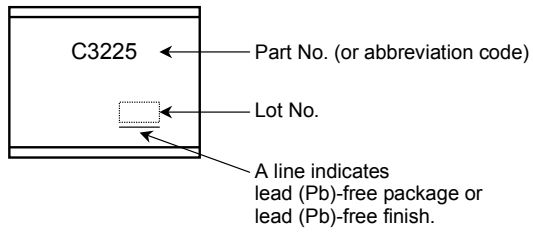


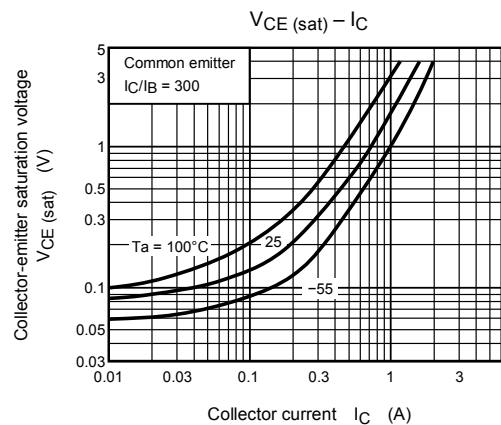
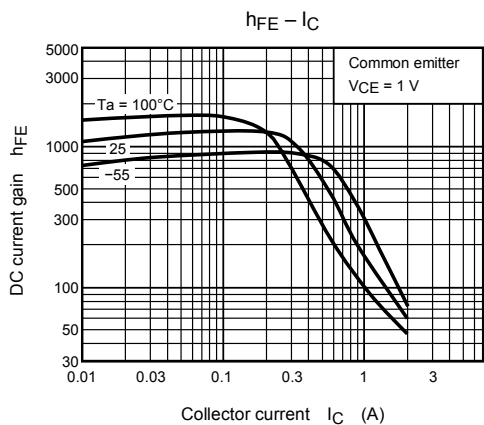
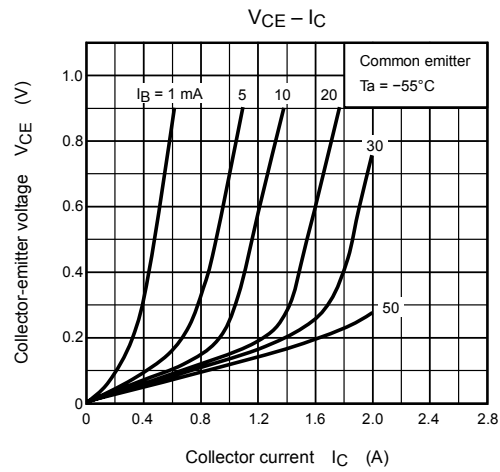
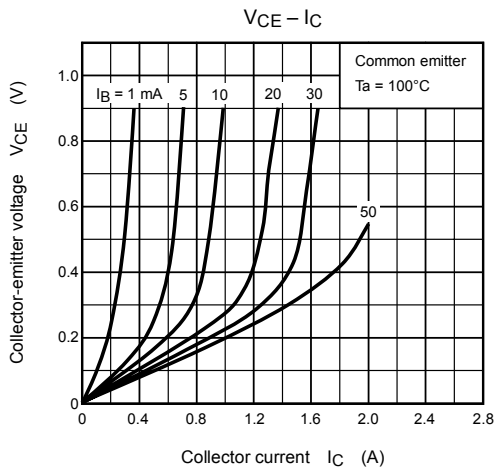
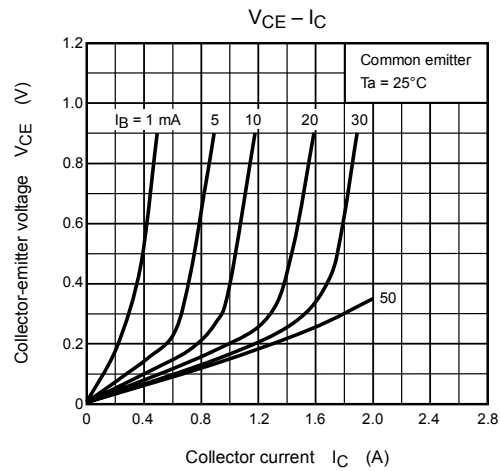
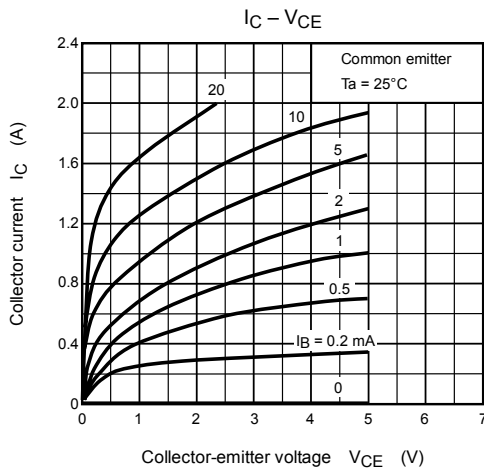
Weight: 0.36 g (typ.)

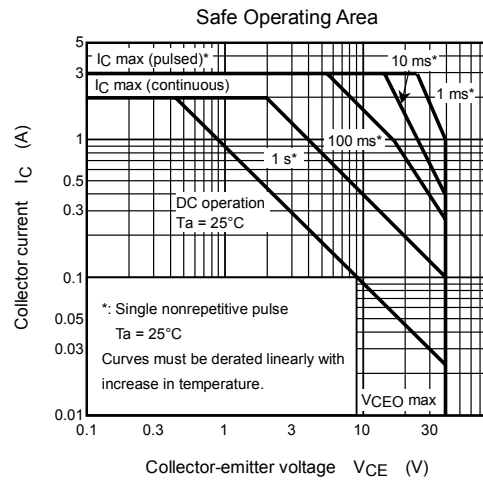
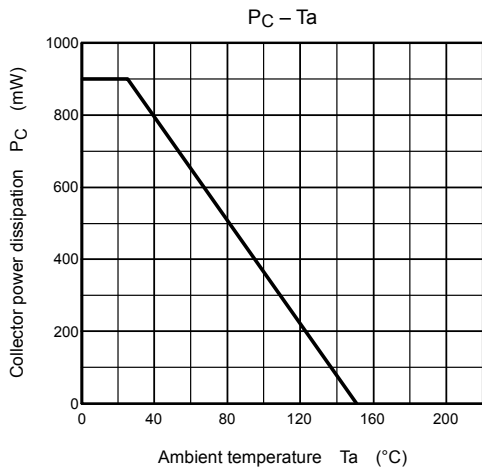
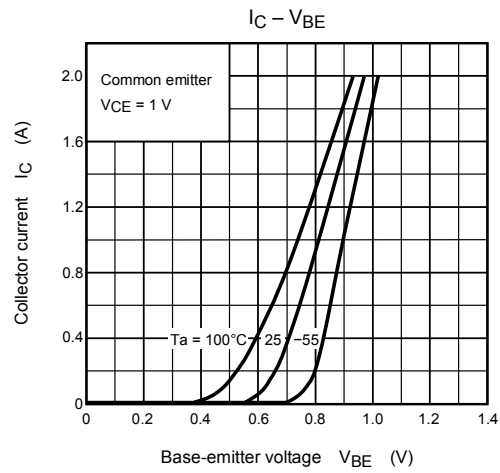
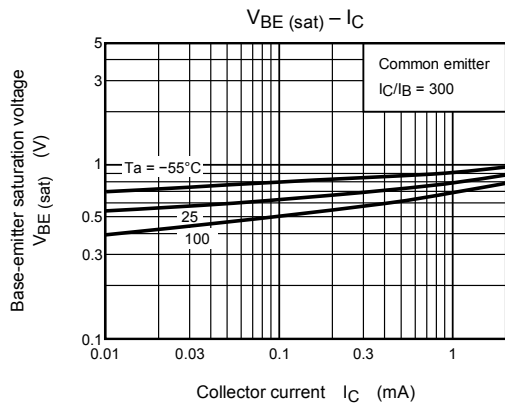
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit				
Collector cut-off current	I_{CBO}	$V_{CB} = 40$ V, $I_E = 0$	—	—	10	μ A				
Emitter cut-off current	I_{EBO}	$V_{EB} = 7$ V, $I_C = 0$	—	—	1	μ A				
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10$ mA, $I_B = 0$	40	—	—	V				
DC current gain	h_{FE}	$V_{CE} = 1$ V, $I_C = 400$ mA	500	—	—					
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300$ mA, $I_B = 1$ mA	—	0.3	0.5	V				
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 300$ mA, $I_B = 1$ mA	—	—	1.1	V				
Transition frequency	f_T	$V_{CB} = 2$ V, $I_C = 100$ mA	—	220	—	MHz				
Collector output capacitance	C_{ob}	$V_{CB} = 10$ V, $I_B = 0$, $f = 1$ MHz	—	20	—	pF				
Switching time	Turn-on time	t_{on}					—	1.0	—	
	Storage time	t_{stg}					—	3.0	—	μ s
	Fall time	t_f					—	1.2	—	

Marking







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